N-Channel 200-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

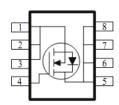
- PoE PSE and PD Circuits
- · LED Inverter Circuits
- 48V-Input DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	I⊳(A)			
200	295 @ V _{GS} = 10V	3		
	$340 @ V_{GS} = 5.5V$	2.7		



FREE





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Limit	Units					
Drain-Source Voltage			200	V				
Gate-Source Voltage	V_{GS}	±20	V					
Continuous Drain Current a	T _A =25°C	· I _D	3					
Continuous Drain Current	T _A =70°C	'D	2.2	Α				
Pulsed Drain Current ^b		I _{DM}	20					
Continuous Source Current (Diode Conduction) a	I _S	4.6	Α					
Power Dissipation ^a	T _A =25°C	P _D	3.5	W				
Fower Dissipation	T _A =70°C	' D	2	VV				
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C				

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
Maximum Junction-to-Ambient	Steady State	IXOJA	81	C/VV			

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

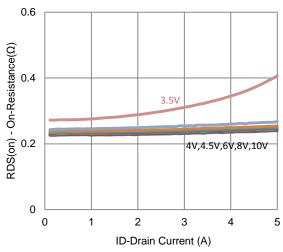
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zoro Coto Voltogo Droin Current	1	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	5			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_{D} = 1 \text{ A}$			295	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, I_D = 0.8 \text{ A}$			340	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 1 \text{ A}$		32		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.76		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 100 \text{ V}, V_{GS} = 5.5 \text{ V},$		9.5			
Gate-Source Charge	Q_{gs}	$I_{D} = 100 \text{ V}, V_{GS} = 3.3 \text{ V},$		2.1		nC	
Gate-Drain Charge	Q_{gd}	10 = 1 A		4.6			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 100 \text{ V}, R_{L} = 100 \Omega,$		8			
Rise Time	t _r	$V_{DS} = 100 \text{ V}, K_L - 100 \Omega,$ $I_D = 1 \text{ A},$		7		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		46		ns	
Fall Time	t _f	VGEN = 10 V, NGEN = 0 12		22			
Input Capacitance	C _{iss}			948			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		80		pF	
Reverse Transfer Capacitance	C_{rss}			54			

Notes

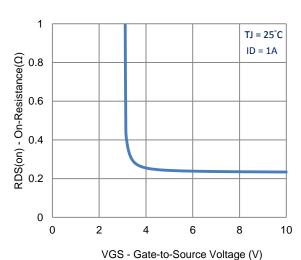
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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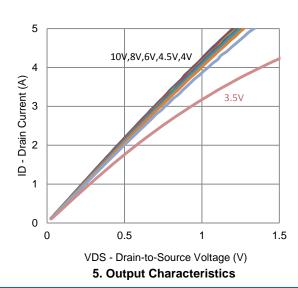
Typical Electrical Characteristics

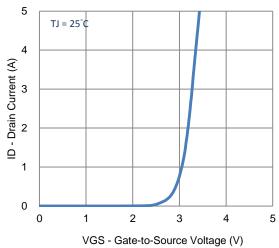


1. On-Resistance vs. Drain Current

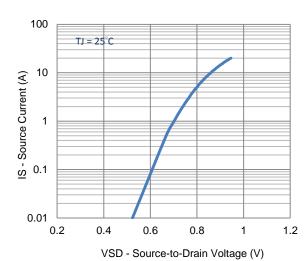


3. On-Resistance vs. Gate-to-Source Voltage

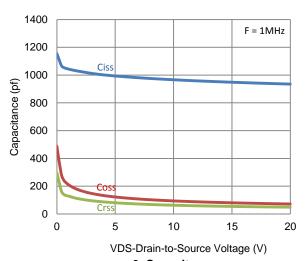




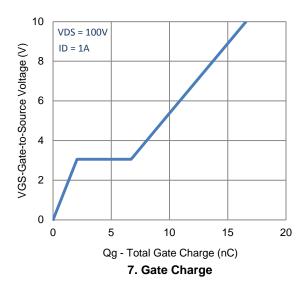
2. Transfer Characteristics

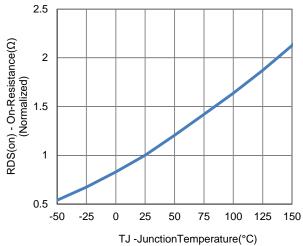


4. Drain-to-Source Forward Voltage

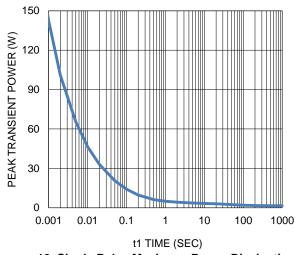


Typical Electrical Characteristics





8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

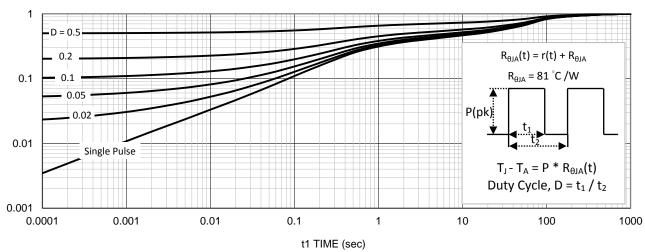
9. Safe Operating Area

100

1000

10

10. Single Pulse Maximum Power Dissipation

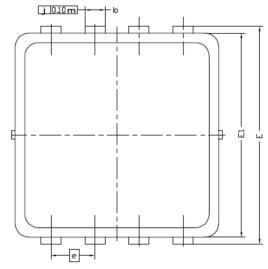


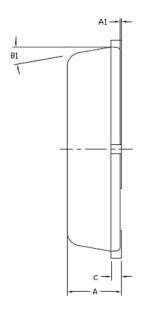
11. Normalized Thermal Transient Junction to Ambient

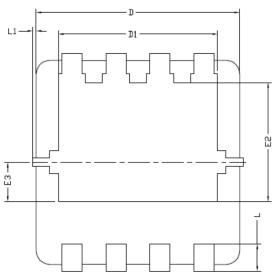
0.01

0.1

Package Information







птм	MILLIMETERS			INCHES			
DIM,	NIM	NDM	MAX	MIN	NDM	MAX	
Α	0,700	0,80	0.900	0,0276	0,0315	0,0354	
A1	0.00		0,05	0,000		0'005	
b	0.24	0.30	0.35	0.009	0.012	0.014	
C	0.10	0.152	0.25	0.004	0.006	0.010	
D	3.00 BSC			0.118 BSC			
D1	2.35 BSC			0.093 BSC			
Ε	3.20 BSC			0,126 BSC			
E1	3.00 B2C			0.118 BSC			
E2	1.75 BSC			0.069 BSC			
E3	0,575 BSC			0.023 BSC			
е	0.65 BSC			0,026 BSC			
L	0,30	0,40	0,50	0,0118	0,0157	0,0197	
L1	0		0,100	0		0,004	
91	0°	10°	12°	0°	10°	12°	